Publikationen

(2020): Wafer composite and method for producing semiconductor components.

(2020): Silicon carbide semiconductor device and a method for forming a silicon carbide semiconductor device.

(2019): Method of manufacturing a semiconductor device having graphene material.

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(2019): Semiconductor device including a heat sink structure.

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(2019): Fahrzeugbeleuchtungsanordnung, Leuchtmitteltreiberschaltung und Verfahren zur Bereitstellung von Informationen zur Bestimmung eines Beleuchtungszustandes.

(2019): Process for the formation of a graphene membrane component, graphene membrane component, microphone and Hall-effect sensor.

(2019): Elektronisches Identifikationsdokument und Verfahren zur Herstellung eines elektronischen Identifikationsdokuments.

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(2018): Sensor arrangement, battery cell and energy system.

(2018): Graphene gas sensor for measuring the concentration of carbon dioxide in gas environments.

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(2018): Semiconductor package, smart card and method for producing a semiconductor package.

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(2017): Method of forming a graphene structure.

(2017): Hall effect sensor with graphene detection layer.

(2017): Two-dimensional material containing electronic components.

(2017): Method for manufacturing a composite wafer having a graphite core, and composite wafer having a graphite core.

(2017): Fluid sensor chip and method for manufacturing the same.

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(2016): Temperature sensor.

(2016): Electronic device.

(2016): Method for processing a carrier and an electronic component.

(2016): Composite wafer for bonding and encapsulation of a SiC-based functional layer.

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